



## **IRFB4310ZPBF Information**

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For Reference Only

Part Number IRFB4310ZPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V 120A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

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# **IRFB4310ZPBF Specifications**

Manufacturer Part Number         IRFB4310ZPBF           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         120A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 150µA           Gate Charge (Qg) (Max) @ Vgs         170nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         6860pF @ 50V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         250W (Tc)           Rds On (Max) @ Id, Vgs         6 mOhm @ 75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		
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Package / Case TO-220-3	Mounting Type	Through Hole
-	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### **IRFB4310ZPBF** Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFB4310ZPBF Payment Methods**



















## **IRFB4310ZPBF Shipping Methods**













If you have any question about IRFB4310ZPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com